## AMENDMENTS TO THE CLAIMS

Claims 1-12 are pending. Please amend claim 1 as follows. The following listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently Amended) ~~Power~~ A power semiconducting device comprising a power component made from a semiconducting material epitaxied on a stacked structure, wherein:

the stacked structure comprises a layer of semiconducting material transferred onto a first face of a support substrate and fixed to the support substrate by an electrically insulating layer, the support substrate comprising electrically conducting means between said first face and a second face, the epitaxied semiconducting material being epitaxied on the transferred layer of semiconducting material ~~acting as an epitaxy support for the epitaxied semiconducting material~~, and

electrical connection means of electrically connecting the ~~device~~ power component are provided, firstly on the epitaxied semiconducting material to provide a first electrical contact to the power component, and secondly on the second face of the support substrate, an electrical connection through the electrically insulating layer and said electrically conducting means of the support substrate electrically connecting ~~the epitaxied semiconducting material~~ a second electrical contact of the power component to the electrically connecting means provided on the second face of the support substrate.

2. (Original) Device according to claim 1, wherein the electrically conducting means of the support substrate are composed of the support substrate itself made of an electrically conducting material.

3. (Original) Device according to claim 1, wherein the epitaxied semiconducting material comprises several layers with a different doping.

4. (Original) Device according to claim 1, wherein the support substrate overdoped on the side of the interface on which the electrically insulating layer is provided.

5. (Original) Device according to claim 1, wherein the electrically conducting means of the device comprise at least one Schottky contact.

6. (Original) Device according to claim 1, wherein the electrically conducting means of the device comprise at least one resistive contact.

7. (Original) Device according to claim 1, wherein the support substrate is made from a semiconducting material.

8. (Original) Device according to claim 7, wherein the support substrate is made from a semiconducting material chosen from among SiC, GaN, AlN, Si, GaAs, ZnO and Ge.

9. (Original) Device according to claim 1, wherein the material used to make the electrically insulating layer may be chosen from among SiO2, Si3N4 and diamond.

10. (Original) Device according to claim 1, wherein the transferred thin layer of semiconducting material is made from a material chosen from among SiC, GaN, AlN, Si, ZnO and diamond.

11. (Original) Device according to claim 1, wherein the epitaxied semiconducting material is chosen from among SiC, GaN, AlGaN, InGaN and diamond.

12. (Previously Presented) Semiconducting circuit, wherein it combines at least one power semiconducting device according to claim 1 and at least one semiconducting device that is not electrically connected to the second face of the support substrate.